

APPLICATION DATA SHEET

Application Information

Application Type::	Regular
Subject Matter::	Utility
Title::	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON
Attorney Docket Number::	MEMC 98-3052 (2512.2)
Request for Early Publication?::	No
Request for Non-Publication?::	No
Total Drawing Sheets::	35
Small Entity?::	No
Petition Included?::	No
Secrecy Order in Parent?::	No

Applicant Information

Applicant Authority Type::	Inventor
Primary Citizenship Country::	US
Status::	Full Capacity
Given Name::	Robert
Middle Name::	J.
Family Name::	Falster
City of Residence::	London
Country of Residence::	England
Street of Mailing Address::	508 Pearl Drive, P.O. Box 8
City of Mailing Address::	St. Peters
State or Province of Mailing Address::	MO
Postal Code of Mailing Address::	63376

Correspondence Information

Correspondence Customer Number:: 000321

Representative Information

Representative Customer Number:: 000321

Domestic Priority Information

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This application	Division of	09/737,715	12/15/00
09/737,715	Continuation of	09/387,288	08/31/99
09/387,288	Non-Provisional of	60/098,902	09/02/98

Assignee Information

Assignee Name::

MEMC Electronic Materials, Inc.